## **Analog Multiplexers/ Demultiplexers**

**High-Performance Silicon-Gate CMOS** 

### MC74HC4051A, MC74HC4052A, MC74HC4053A

The MC74HC4051A, MC74HC4052A and MC74HC4053A utilize silicon-gate CMOS technology to achieve fast propagation delays, low ON resistances, and low OFF leakage currents. These analog multiplexers/demultiplexers control analog voltages that may vary across the complete power supply range (from V<sub>CC</sub> to V<sub>EE</sub>).

The HC4051A, HC4052A and HC4053A are identical in pinout to the metal-gate MC14051AB, MC14052AB and MC14053AB. The Channel-Select inputs determine which one of the Analog Inputs/Outputs is to be connected, by means of an analog switch, to the Common Output/Input. When the Enable pin is HIGH, all analog switches are turned off.

The Channel-Select and Enable inputs are compatible with standard CMOS outputs; with pullup resistors they are compatible with LSTTL

These devices have been designed so that the ON resistance (Ron) is more linear over input voltage than Ron of metal-gate CMOS analog

For a multiplexer/demultiplexer with injection current protection, see HC4851A and HC4852A.

#### **Features**

- Fast Switching and Propagation Speeds
- Low Crosstalk Between Switches
- Diode Protection on All Inputs/Outputs
- Analog Power Supply Range  $(V_{CC} V_{EE}) = 2.0$  to 12.0 V
- Digital (Control) Power Supply Range ( $V_{CC}$  GND) = 2.0 to 6.0 V
- Improved Linearity and Lower ON Resistance Than Metal-Gate Counterparts
- Low Noise
- In Compliance with the Requirements of JEDEC Standard No. 7A
- Chip Complexity: HC4051A 184 FETs or 46 Equivalent Gates HC4052A - 168 FETs or 42 Equivalent Gates HC4053A - 156 FETs or 39 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR-Free and are RoHS Compliant

This document contains information on some products that are still under development. ON Semiconductor reserves the right to change or discontinue these products without notice.



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TSSOP-16 **DT SUFFIX** CASE 948F

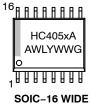


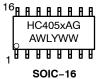
SOIC-16 **D SUFFIX CASE 751B** 



**MN SUFFIX** CASE 485AW

#### **MARKING DIAGRAMS**









TSSOP-16

= Assembly Location

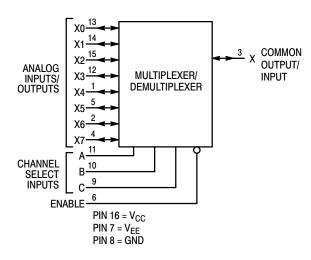
WL, L = Wafer Lot YY, Y = Year WW, W = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 13 of this data sheet.

### LOGIC DIAGRAM MC74HC4051A Single-Pole, 8-Position Plus Common Off

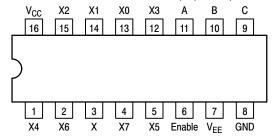


### **FUNCTION TABLE - MC74HC4051A**

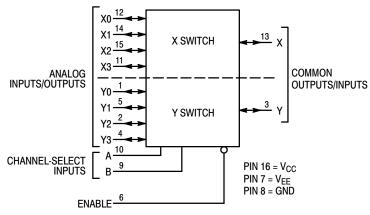
Conti	rol In			
	,	Selec	t	
Enable	С	В	Α	ON Channels
L	L	L	L	X0
L	L	L	Н	X1
L	L	Н	L	X2
L	L	Н	Н	X3
L	Н	L	L	X4
L	Н	L	Н	X5
L	Н	Н	L	X6
L	Н	Н	Н	X7
H	X	Χ	Χ	NONE

X = Don't Care

### Pinout: MC74HC4051A (Top View)



### LOGIC DIAGRAM MC74HC4052A Double-Pole, 4-Position Plus Common Off

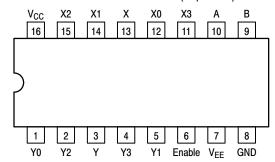


### **FUNCTION TABLE - MC74HC4052A**

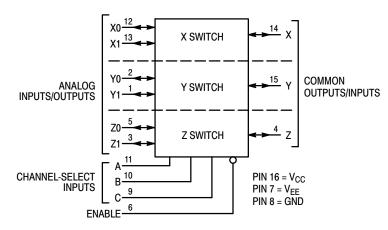
Contr	ol Input	s			
	Select				
Enable	В	Α	ON Ch	annels	
L	L	L	Y0	X0	
L	L	Н	Y1	X1	
L	Н	L	Y2	X2	
L	Н	Н	Y3	X3	
Н	Χ	Χ	NONE		

X = Don't Care

### Pinout: MC74HC4052A (Top View)



# LOGIC DIAGRAM MC74HC4053A Triple Single-Pole, Double-Position Plus Common Off



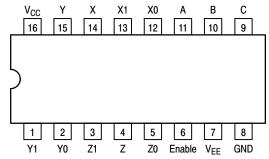
NOTE: This device allows independent control of each switch. Channel–Select Input A controls the X–Switch, Input B controls the Y–Switch and Input C controls the Z–Switch

### **FUNCTION TABLE - MC74HC4053A**

Control Inputs							
Enable	С	Selec B	t A	10	l Chann	els	
L	L	L	L	Z0	Y0	X0	
L	L	L	Н	Z0	Y0	X1	
L	L	Н	L	Z0	Y1	X0	
L	L	Н	Н	Z0	Y1	X1	
L	Н	L	L	Z1	Y0	X0	
L	H	L	Н	Z1	Y0	X1	
L	H	Н	L	Z1	Y1	X0	
L	Н	Н	Н	Z1 Y1 X1			
Н	X	Χ	Χ		NONE		

X = Don't Care

### Pinout: MC74HC4053A (Top View)



### **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Positive DC Supply Voltage (Referenced to GND) (Referenced to V <sub>EE</sub> )	-0.5 to +7.0 -0.5 to +14.0	V
V <sub>EE</sub>	Negative DC Supply Voltage (Referenced to GND)	-7.0 to +5.0	V
V <sub>IS</sub>	Analog Input Voltage	V <sub>EE</sub> – 0.5 to V <sub>CC</sub> + 0.5	V
V <sub>in</sub>	Digital Input Voltage (Referenced to GND)	-0.5 to V <sub>CC</sub> + 0.5	V
I	DC Current, Into or Out of Any Pin	±25	mA
P <sub>D</sub>	Power Dissipation in Still Air, SOIC Package† TSSOP Package†	500 450	mW
T <sub>stg</sub>	Storage Temperature Range	-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds SOIC or TSSOP Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{\rm CC}$ ). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating: SOIC Package: -7 mW/°C from 65° to 125°C TSSOP Package: -6.1 mW/°C from 65° to 125°C

#### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V <sub>CC</sub>	Positive DC Supply Voltage	(Referenced to GND) (Referenced to V <sub>EE</sub> )	2.0 2.0	6.0 12.0	V
V <sub>EE</sub>	Negative DC Supply Voltage, Output (Referenced to GND)		-6.0	GND	V
V <sub>IS</sub>	Analog Input Voltage		V <sub>EE</sub>	V <sub>CC</sub>	V
V <sub>in</sub>	Digital Input Voltage (Referenced to GND)		GND	V <sub>CC</sub>	V
V <sub>IO</sub> *	Static or Dynamic Voltage Across Switch			1.2	V
T <sub>A</sub>	Operating Temperature Range, All Package Types		<b>–</b> 55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise/Fall Time (Channel Select or Enable Inputs)	$V_{CC} = 2.0 \text{ V}$ $V_{CC} = 3.0 \text{ V}$ $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$	0 0 0	1000 600 500 400	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond

### DC CHARACTERISTICS — Digital Section (Voltages Referenced to GND) VEE = GND, Except Where Noted

				V <sub>CC</sub>	Guara	nteed Lim	nit	
Symbol	Parameter	Conditio	n	V	-55 to 25°C	≤ <b>85</b> °C	≤125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage, Channel-Select or Enable Inputs	R <sub>on</sub> = Per Spec		2.0 3.0 4.5 6.0	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	V
V <sub>IL</sub>	Maximum Low-Level Input Voltage, Channel-Select or Enable Inputs	R <sub>on</sub> = Per Spec		2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	V
l <sub>in</sub>	Maximum Input Leakage Current, Channel-Select or Enable Inputs	$V_{in} = V_{CC}$ or GND, $V_{EE} = -6.0 \text{ V}$		6.0	± 0.1	± 1.0	± 1.0	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	Channel Select, Enab $V_{IS} = V_{CC}$ or GND; $V_{IO} = 0 \text{ V}$		6.0 6.0	1 4	10 40	20 80	μΑ

the Recommended Operating Ranges limits may affect device reliability.

\*For voltage drops across switch greater than 1.2 V (switch on), excessive V<sub>CC</sub> current may be drawn; i.e., the current out of the switch may contain both V<sub>CC</sub> and switch input components. The reliability of the device will be unaffected unless the Maximum Ratings are exceeded.

### DC CHARACTERISTICS — Analog Section

					Guara	nteed Lim	nit	
Symbol	Parameter	Condition	V <sub>CC</sub>	V <sub>EE</sub>	−55 to 25°C	≤ <b>85</b> °C	≤125°C	Unit
R <sub>on</sub>	Maximum "ON" Resistance	$V_{in} = V_{IL}$ or $V_{IH}$ ; $V_{IS} = V_{CC}$ to $V_{EE}$ ; $I_S \le 2.0$ mA (Figures 1, 2)	4.5 4.5 6.0	0.0 - 4.5 - 6.0	190 120 100	240 150 125	280 170 140	Ω
		$\begin{aligned} &V_{in} = V_{IL} \text{ or } V_{IH}; \ V_{IS} = V_{CC} \text{ or } \\ &V_{EE} \text{ (Endpoints); } I_{S} \leq 2.0 \text{ mA} \\ &\text{(Figures 1, 2)} \end{aligned}$	4.5 4.5 6.0	0.0 - 4.5 - 6.0	150 100 80	190 125 100	230 140 115	
$\Delta R_{on}$	Maximum Difference in "ON" Resistance Between Any Two Channels in the Same Package	$\begin{split} &V_{in} = V_{IL} \text{ or } V_{IH}; \\ &V_{IS} = 1/2  (V_{CC} - V_{EE}); \\ &I_S \leq 2.0 \text{ mA} \end{split}$	4.5 4.5 6.0	0.0 - 4.5 - 6.0	30 12 10	35 15 12	40 18 14	Ω
l <sub>off</sub>	Maximum Off-Channel Leakage Current, Any One Channel	$V_{in} = V_{IL} \text{ or } V_{IH};$ $V_{IO} = V_{CC} - V_{EE};$ Switch Off (Figure 3)	6.0	- 6.0	0.1	0.5	1.0	μΑ
	Maximum Off-ChannelHC4051A Leakage Current, HC4052A Common Channel HC4053A	$V_{IO} = V_{CC} - V_{EE};$	6.0 6.0 6.0	- 6.0 - 6.0 - 6.0	0.2 0.1 0.1	2.0 1.0 1.0	4.0 2.0 2.0	
l <sub>on</sub>	Maximum On-ChannelHC4051A Leakage Current, HC4052A Channel-to-Channel HC4053A	Switch-to-Switch =	6.0 6.0 6.0	- 6.0 - 6.0 - 6.0	0.2 0.1 0.1	2.0 1.0 1.0	4.0 2.0 2.0	μΑ

### **AC CHARACTERISTICS** ( $C_L = 50 \text{ pF}$ , Input $t_r = t_f = 6 \text{ ns}$ )

			V <sub>CC</sub>	Guara	nteed Lin	nit	
Symbol	Parameter		v	-55 to 25°C	≤ <b>85</b> °C	≤125°C	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Channel-Select to Ana (Figure 9)	log Output	2.0 3.0 4.5 6.0	270 90 59 45	320 110 79 65	350 125 85 75	ns
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Analog Input to Analog (Figure 10)	Output	2.0 3.0 4.5 6.0	40 25 12 10	60 30 15 13	70 32 18 15	ns
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Maximum Propagation Delay, Enable to Analog Outpu (Figure 11)	ut	2.0 3.0 4.5 6.0	160 70 48 39	200 95 63 55	220 110 76 63	ns
t <sub>PZL</sub> , t <sub>PZH</sub>	Maximum Propagation Delay, Enable to Analog Output (Figure 11)	ut	2.0 3.0 4.5 6.0	245 115 49 39	315 145 69 58	345 155 83 67	ns
C <sub>in</sub>	Maximum Input Capacitance, Channel-Select or Ena	ble Inputs		10	10	10	pF
C <sub>I/O</sub>	Maximum Capacitance (All Switches Off) Common	Analog I/O O/I: HC4051A HC4052A HC4053A		35 130 80 50	35 130 80 50	35 130 80 50	pF
		Feed-through		1.0	1.0	1.0	
			Typica	il @ 25°C, V <sub>CC</sub>		/ <sub>EE</sub> = 0 V	_
C <sub>PD</sub>	Power Dissipation Capacitance (Figure 13)*	HC4051A HC4052A HC4053A		45 80 45			pF

<sup>\*</sup> Used to determine the no–load dynamic power consumption:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ .

### ADDITIONAL APPLICATION CHARACTERISTICS (GND = 0 V)

	Ve		v <sub>cc</sub>	V <sub>EE</sub>	Limit*			
Symbol	Parameter	Condition	V	V	25°C			Unit
BW	Maximum On-Channel Bandwidth or Minimum Frequency Response (Figure 6)	f <sub>in</sub> = 1MHz Sine Wave; Adjust f <sub>in</sub> Voltage to Obtain 0dBm at V <sub>OS</sub> ; Increase f <sub>in</sub> Frequency Until dB Meter Reads –3dB;	2.25	-2.25	'51 80	'52 95	'53 120	MHz
	(i igure o)	$R_L = 50\Omega$ , $C_L = 10pF$	4.50 6.00	-4.50 -6.00	80 80	95 95	120 120	
-	Off-Channel Feed-through Isolation (Figure 7)	$f_{in}$ = Sine Wave; Adjust $f_{in}$ Voltage to Obtain 0dBm at $V_{IS}$ $f_{in}$ = 10kHz, $R_L$ = 600 $\Omega$ , $C_L$ = 50pF	2.25 4.50 6.00	-2.25 -4.50 -6.00		-50 -50 -50		dB
		f <sub>in</sub> = 1.0MHz, R <sub>L</sub> = 50Ω, C <sub>L</sub> = 10pF	2.25 4.50 6.00	-2.25 -4.50 -6.00		-40 -40 -40		
-	Feedthrough Noise. Channel-Select Input to Common I/O (Figure 8)	$\begin{split} &V_{in} \leq \text{1MHz Square Wave } (t_r = t_f = 6\text{ns}); \\ &\text{Adjust R}_L \text{ at Setup so that } I_S = 0\text{A}; \\ &\text{Enable} = \text{GND} \qquad R_L = 600\Omega, \ C_L = 50\text{pF} \end{split}$	2.25 4.50 6.00	-2.25 -4.50 -6.00		25 105 135		mV <sub>PP</sub>
		$R_L$ = 10kΩ, $C_L$ = 10pF	2.25 4.50 6.00	-2.25 -4.50 -6.00		35 145 190		
-	Crosstalk Between Any Two Switches (Figure 12) (Test does not apply to HC4051A)	$f_{in}$ = Sine Wave; Adjust $f_{in}$ Voltage to Obtain 0dBm at $V_{IS}$ $f_{in}$ = 10kHz, $R_L$ = 600 $\Omega$ , $C_L$ = 50pF	2.25 4.50 6.00	-2.25 -4.50 -6.00		-50 -50 -50		dB
		$f_{in}$ = 1.0MHz, $R_L$ = 50 $\Omega$ , $C_L$ = 10pF	2.25 4.50 6.00	-2.25 -4.50 -6.00		-60 -60 -60		
THD	Total Harmonic Distortion (Figure 14)	$f_{\text{in}}$ = 1kHz, R <sub>L</sub> = 10k $\Omega$ , C <sub>L</sub> = 50pF THD = THD <sub>measured</sub> – THD <sub>source</sub>						%
		$V_{IS} = 4.0V_{PP}$ sine wave $V_{IS} = 8.0V_{PP}$ sine wave $V_{IS} = 11.0V_{PP}$ sine wave	2.25 4.50 6.00	-2.25 -4.50 -6.00		0.10 0.08 0.05		

<sup>\*</sup>Limits not tested. Determined by design and verified by qualification.

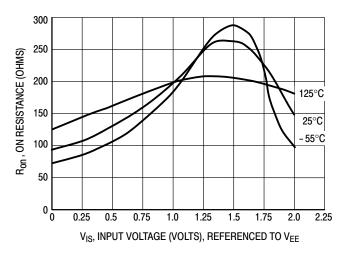


Figure 1a. Typical On Resistance,  $V_{CC}$  –  $V_{EE}$  = 2.0 V

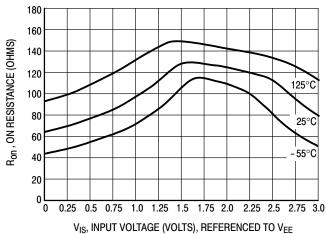
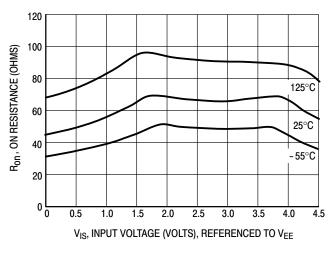


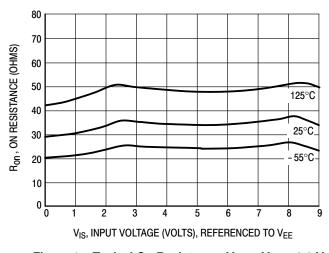
Figure 1b. Typical On Resistance,  $V_{CC}$  –  $V_{EE}$  = 3.0 V



105 90 75 60 45 0 0 0.5 1.0 1.5 2.0 2.5 3.0 3.5 4.0 4.5 5.0 5.5 6.0 V<sub>IS</sub>, INPUT VOLTAGE (VOLTS), REFERENCED TO V<sub>EE</sub>

Figure 1c. Typical On Resistance,  $V_{CC}$  –  $V_{EE}$  = 4.5 V

Figure 1d. Typical On Resistance,  $V_{CC} - V_{EE} = 6.0 \text{ V}$ 



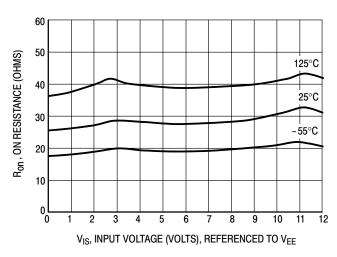


Figure 1e. Typical On Resistance,  $V_{CC}$  –  $V_{EE}$  = 9.0 V

Figure 1f. Typical On Resistance,  $V_{CC}$  –  $V_{EE}$  = 12.0 V

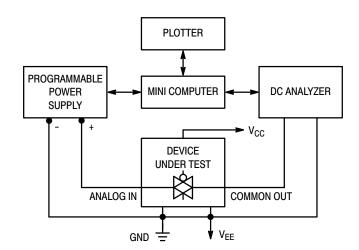


Figure 2. On Resistance Test Set-Up

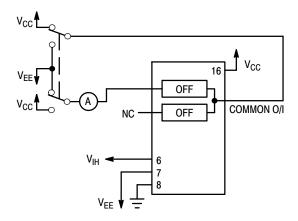


Figure 3. Maximum Off Channel Leakage Current, Any One Channel, Test Set-Up

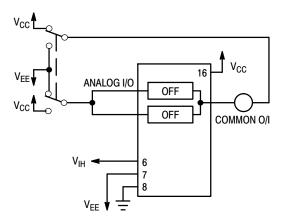


Figure 4. Maximum Off Channel Leakage Current, Common Channel, Test Set-Up

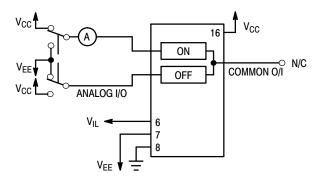


Figure 5. Maximum On Channel Leakage Current, Channel to Channel, Test Set-Up

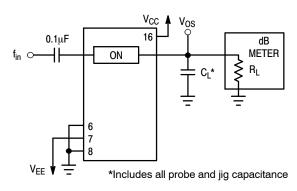


Figure 6. Maximum On Channel Bandwidth, Test Set-Up

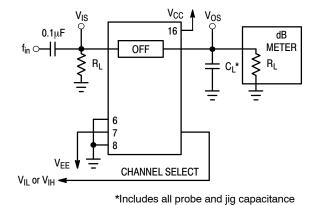
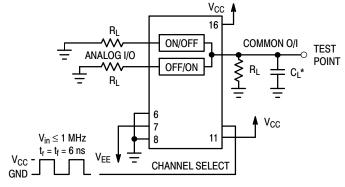


Figure 7. Off Channel Feedthrough Isolation, Test Set-Up



\*Includes all probe and jig capacitance

Figure 8. Feedthrough Noise, Channel Select to Common Out, Test Set-Up

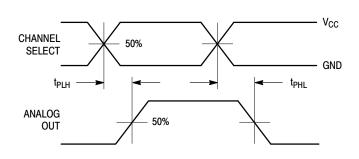
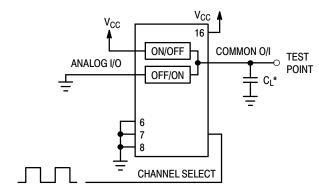


Figure 9a. Propagation Delays, Channel Select to Analog Out



\*Includes all probe and jig capacitance

Figure 9b. Propagation Delay, Test Set-Up Channel Select to Analog Out

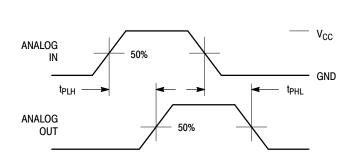
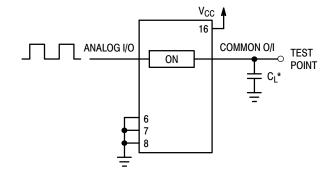


Figure 10a. Propagation Delays, Analog In to Analog Out



\*Includes all probe and jig capacitance

Figure 10b. Propagation Delay, Test Set-Up Analog In to Analog Out

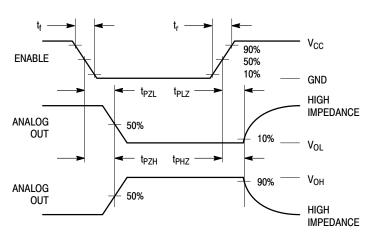


Figure 11a. Propagation Delays, Enable to Analog Out

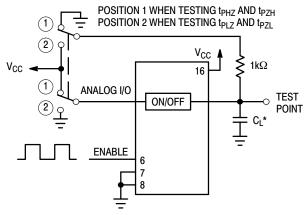
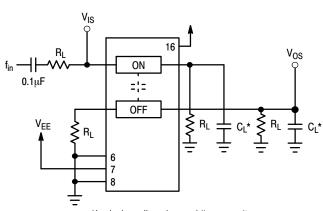


Figure 11b. Propagation Delay, Test Set-Up
Enable to Analog Out



\*Includes all probe and jig capacitance

Figure 12. Crosstalk Between Any Two Switches, Test Set-Up

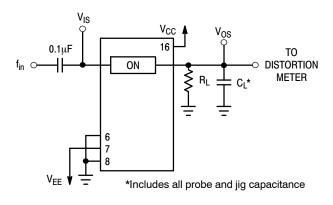


Figure 14a. Total Harmonic Distortion, Test Set-Up

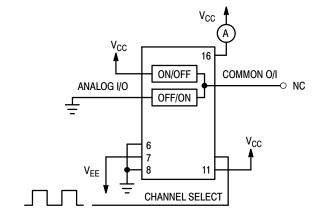


Figure 13. Power Dissipation Capacitance, Test Set-Up

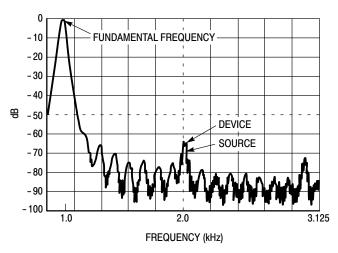


Figure 14b. Plot, Harmonic Distortion

### **APPLICATIONS INFORMATION**

The Channel Select and Enable control pins should be at  $V_{CC}$  or GND logic levels.  $V_{CC}$  being recognized as a logic high and GND being recognized as a logic low. In this example:

$$V_{CC}$$
 = +5V = logic high  
GND = 0V = logic low

The maximum analog voltage swings are determined by the supply voltages  $V_{CC}$  and  $V_{EE}$ . The positive peak analog voltage should not exceed  $V_{CC}$ . Similarly, the negative peak analog voltage should not go below  $V_{EE}$ . In this example, the difference between  $V_{CC}$  and  $V_{EE}$  is ten volts. Therefore, using the configuration of Figure 15, a maximum analog signal of ten volts peak—to—peak can be controlled. Unused analog inputs/outputs may be left floating (i.e., not connected). However, tying unused analog inputs and

outputs to  $V_{CC}$  or GND through a low value resistor helps minimize crosstalk and feed-through noise that may be picked up by an unused switch.

Although used here, balanced supplies are not a requirement. The only constraints on the power supplies are that:

$$\begin{split} V_{CC} - GND &= 2 \text{ to 6 volts} \\ V_{EE} - GND &= 0 \text{ to -6 volts} \\ V_{CC} - V_{EE} &= 2 \text{ to 12 volts} \\ and V_{EE} &\leq GND \end{split}$$

When voltage transients above  $V_{CC}$  and/or below  $V_{EE}$  are anticipated on the analog channels, external Germanium or Schottky diodes  $(D_x)$  are recommended as shown in Figure 16. These diodes should be able to absorb the maximum anticipated current surges during clipping.

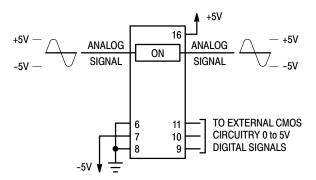


Figure 15. Application Example

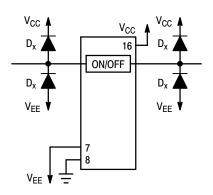
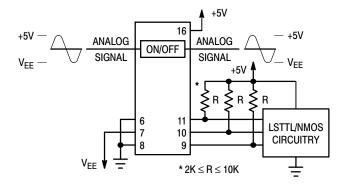
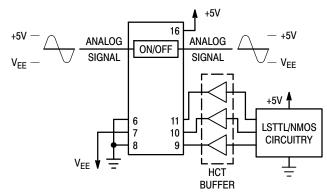


Figure 16. External Germanium or **Schottky Clipping Diodes** 

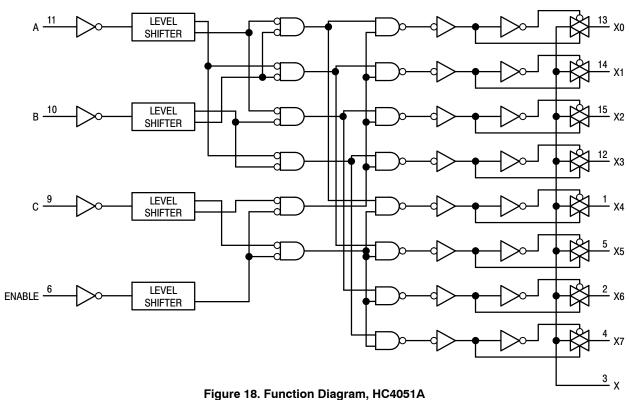


a. Using Pull-Up Resistors



b. Using HCT Interface

Figure 17. Interfacing LSTTL/NMOS to CMOS Inputs



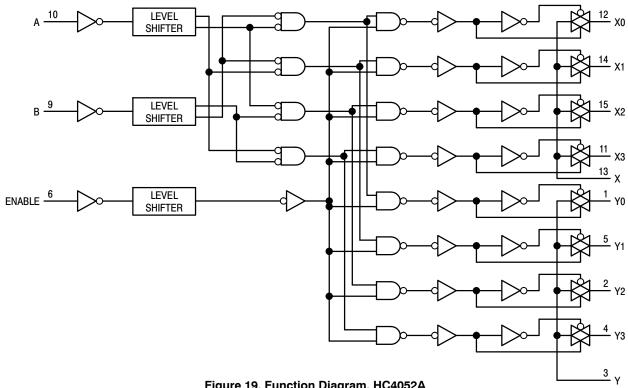


Figure 19. Function Diagram, HC4052A

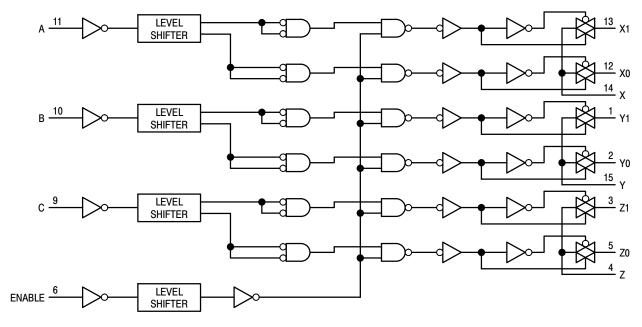


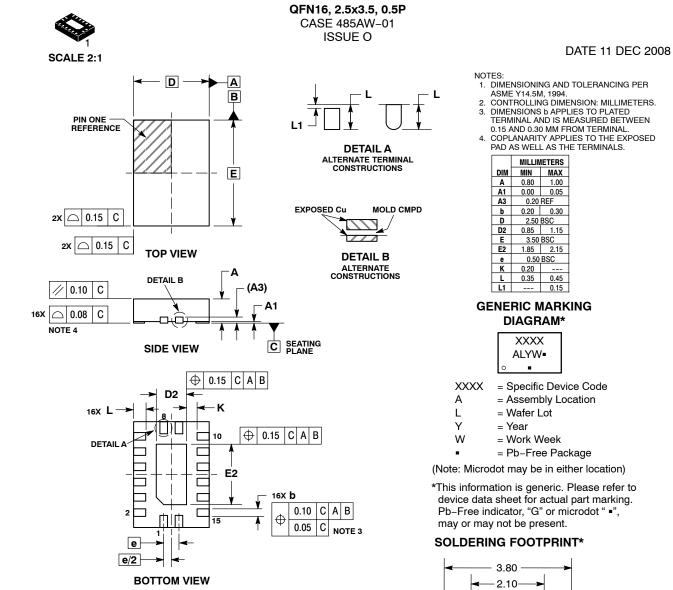
Figure 20. Function Diagram, HC4053A

### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>		
MC74HC4051ADG		48 Units / Rail		
MC74HC4051ADR2G		2500 Units / Tape & Reel		
NLV74HC4051ADR2G*	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel		
MC74HC4051AADR2G	(. 2	2500 Units / Tape & Reel		
NLV74HC4051AADR2G*		2500 Units / Tape & Reel		
MC74HC4051ADWG		48 Units / Rail		
MC74HC4051ADWR2G	SOIC-16 WIDE (Pb-Free)	1000 Units / Tape & Reel		
NLVHC4051ADWR2G*	(121133)	1000 Units / Tape & Reel		
MC74HC4051ADTG		96 Units / Rail		
MC74HC4051ADTR2G	TSSOP-16	2500 Units / Tape & Reel		
NLVHC4051ADTR2G*	(Pb-Free)	2500 Units / Tape & Reel		
NLVHC4051AADTR2G*		2500 Units / Tape & Reel		
NLVHC4051AMNTWG* (In Development)	QFN16 (Pb-Free)	3000 Units / Tape & Reel		
MC74HC4052ADG	SOIC-16	48 Units / Rail		
MC74HC4052ADR2G	(Pb-Free)	2500 Units / Tape & Reel		
NLV74HC4052ADR2G*		2500 Units / Tape & Reel		
MC74HC4052ADWG	SOIC-16 WIDE	48 Units / Rail		
MC74HC4052ADWR2G	(Pb-Free)	1000 Units / Tape & Reel		
MC74HC4052ADTG	_	96 Units / Rail		
MC74HC4052ADTR2G	TSSOP-16	2500 Units / Tape & Reel		
NLV74HC4052ADTRG*	(Pb-Free)	2500 Units / Tape & Reel		
NLVHC4052ADTR2G*		2500 Units / Tape & Reel		
NLVHC4052AMNTWG* (In Development)	QFN16 (Pb-Free)	3000 Units / Tape & Reel		
MC74HC4053ADG		48 Units / Rail		
MC74HC4053ADR2G	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel		
NLV74HC4053ADR2G*	(1.5 -1.100)	2500 Units / Tape & Reel		
MC74HC4053ADWG		48 Units / Rail		
NLV74HC4053ADWRG*	SOIC-16 WIDE	1000 Units / Tape & Reel		
MC74HC4053ADWR2G	(Pb-Free)	1000 Units / Tape & Reel		
NLV74HC4053ADWR2G*		1000 Units / Tape & Reel		
MC74HC4053ADTG		96 Units / Rail		
MC74HC4053ADTR2G	TSSOP-16 (Pb-Free)	2500 Units / Tape & Reel		
NLVHC4053ADTR2G*	(. 2	2500 Units / Tape & Reel		

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

16X

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DIMENSIONS: MILLIMETERS

DESCRIPTION:	QFN16, 2.5X3.5, 0.5P		PAGE 1 OF 1
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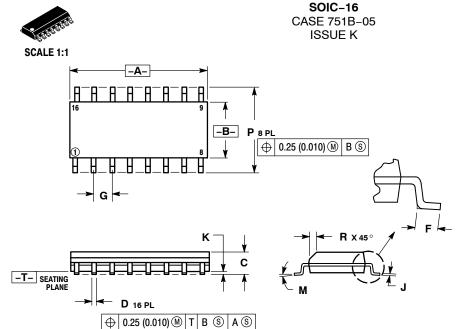
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0.50 PITCH

PACKAGE



**DATE 29 DEC 2006** 

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
  DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

  MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

  DIMENSION D DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

  SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

  DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:			
	COLLECTOR		CATHODE	PIN 1.	COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DY	E#1	
2.			ANODE	2.	BASE, #1	2.	COLLECTOR, #1		
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	COLLECTOR, #2		
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2		
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3		
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3		
7.	COLLECTOR	7.		7.	EMITTER, #2	7.	COLLECTOR, #4		
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4		
9.	BASE		CATHODE	9.	COLLECTOR, #3	9.	BASE, #4		
10.	EMITTER		ANODE	10.	BASE, #3	10.	EMITTER, #4		
11.			NO CONNECTION	11.	EMITTER, #3	11.	BASE, #3		
12.	EMITTER		CATHODE	12.	COLLECTOR, #3	12.	EMITTER, #3		
13.	BASE		CATHODE	13.	COLLECTOR, #4	13.	BASE, #2	SOI DED	ING FOOTPRINT
14.			NO CONNECTION	14.	BASE, #4	14.	EMITTER, #2	SOLDEN	IING FOOTFRINT
15.	EMITTER	15.		15.	EMITTER, #4	15.	BASE, #1		8X
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1	◄	— 6.40 —— <del>&gt;</del>
								"	0.10
STYLE 5:		STYLE 6:		STYLE 7:					16X 1.12
PIN 1.	DRAIN, DYE #1		CATHODE	PIN 1.	SOURCE N-CH				,
2.	DRAIN, #1	2.	CATHODE	2.	COMMON DRAIN (OUTPUT	Γ)		. $\square_1$	16
3.	DRAIN, #2	3.	CATHODE	3.	COMMON DRAIN (OUTPUT			<b>↓</b> — ·	
4.	DRAIN, #2	4.	CATHODE	4.	GATE P-CH	,			
5.	DRAIN, #3	5.	CATHODE	5.	COMMON DRAIN (OUTPUT	Γ)		16X 🛣	
6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPUT			.58 <sup>T</sup>	' <u> </u>
7.	DRAIN, #4	7.	CATHODE	7.	COMMON DRAIN (OUTPUT		U	.50	·
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH `	,			
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH				
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPUT	Γ)			
11.	GATE, #3	11.	ANODE	11.	COMMON DRAIN (OUTPUT	r)			
12.	SOURCE, #3	12.	ANODE	12.	COMMON DRAIN (OUTPUT	r)			
13.	GATE, #2	13.	ANODE	13.	GATE N-CH	,			
14.	SOURCE, #2	14.	ANODE	14.	COMMON DRAIN (OUTPUT	Γ)			↓ PITCH
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPUT				<u> </u>
16.	SOURCE, #1	16.	ANODE	16.	SOURCE N-CH				
								<u> </u>	9 +-+-
								<b>_</b>	
									DIMENSIONS MILLIMETERS
									DIMENSIONS: MILLIMETERS

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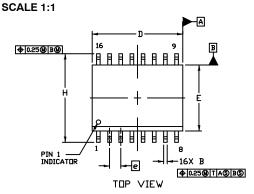


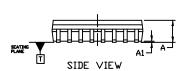


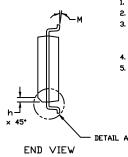
SOIC-16 WB CASE 751G ISSUE E

**DATE 08 OCT 2021** 









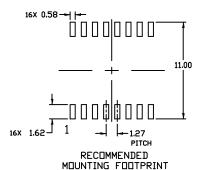


DETAIL A

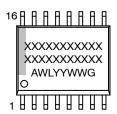
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- CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
- MAXIMUM MOLD PROTRUSION OR FLASH TO BE 0.15 PER SIDE.

	MILLIMETERS			
DIM	MIN.	MAX.		
Α	2.35	2.65		
A1	0.10	0.25		
В	0.35	0.49		
С	0.23	0.32		
D	10.15	10.45		
E	7.40	7.60		
e	1.27	1.27 BSC		
Н	10.05	10.55		
h	0.53 REF			
١	0.50	0.90		
М	0*	7*		



### **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot YY = Year ww = Work Week = Pb-Free Package

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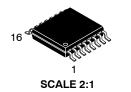
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0.10 (0.004)

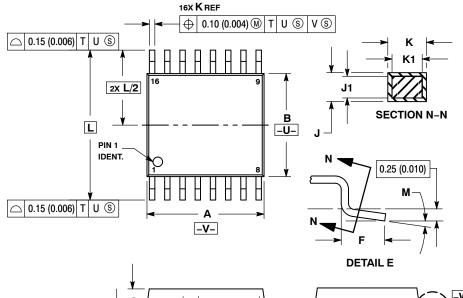
D

-T- SEATING PLANE



TSSOP-16 CASE 948F-01 ISSUE B

**DATE 19 OCT 2006** 



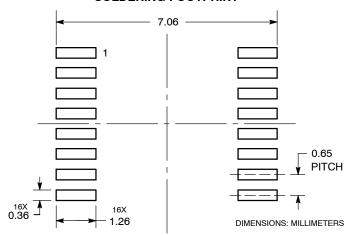
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- JIES:
  DIMENSIONING AND TOLERANCING PER
  ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
  DIMENSION A DOES NOT INCLUDE MOLD
  FLASH. PROTRUSIONS OR GATE BURRS.
  MOLD EL ROLL OF GATE BURDS SUAL NO.
- MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65 BSC		0.026 BSC		
Н	0.18	0.28	0.007	0.011	
7	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40 BSC		0.252 BSC		
М	0 °	8 °	0 °	8 °	

### **SOLDERING FOOTPRINT**

G



### **GENERIC MARKING DIAGRAM\***



XXXX = Specific Device Code Α = Assembly Location

= Wafer Lot L Υ = Year W = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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